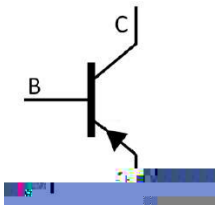
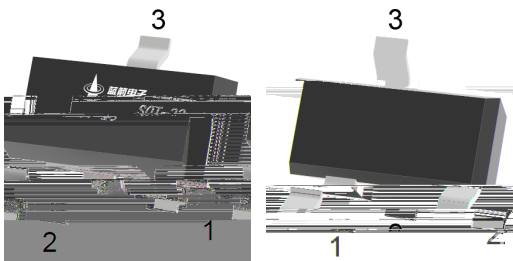


Silicon PNP transistor in a SOT-23 Plastic Package.

Collector currents to 600mA. Halogen free product, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

General purpose amplifier, Meet the stringent requirements of automotive applications.



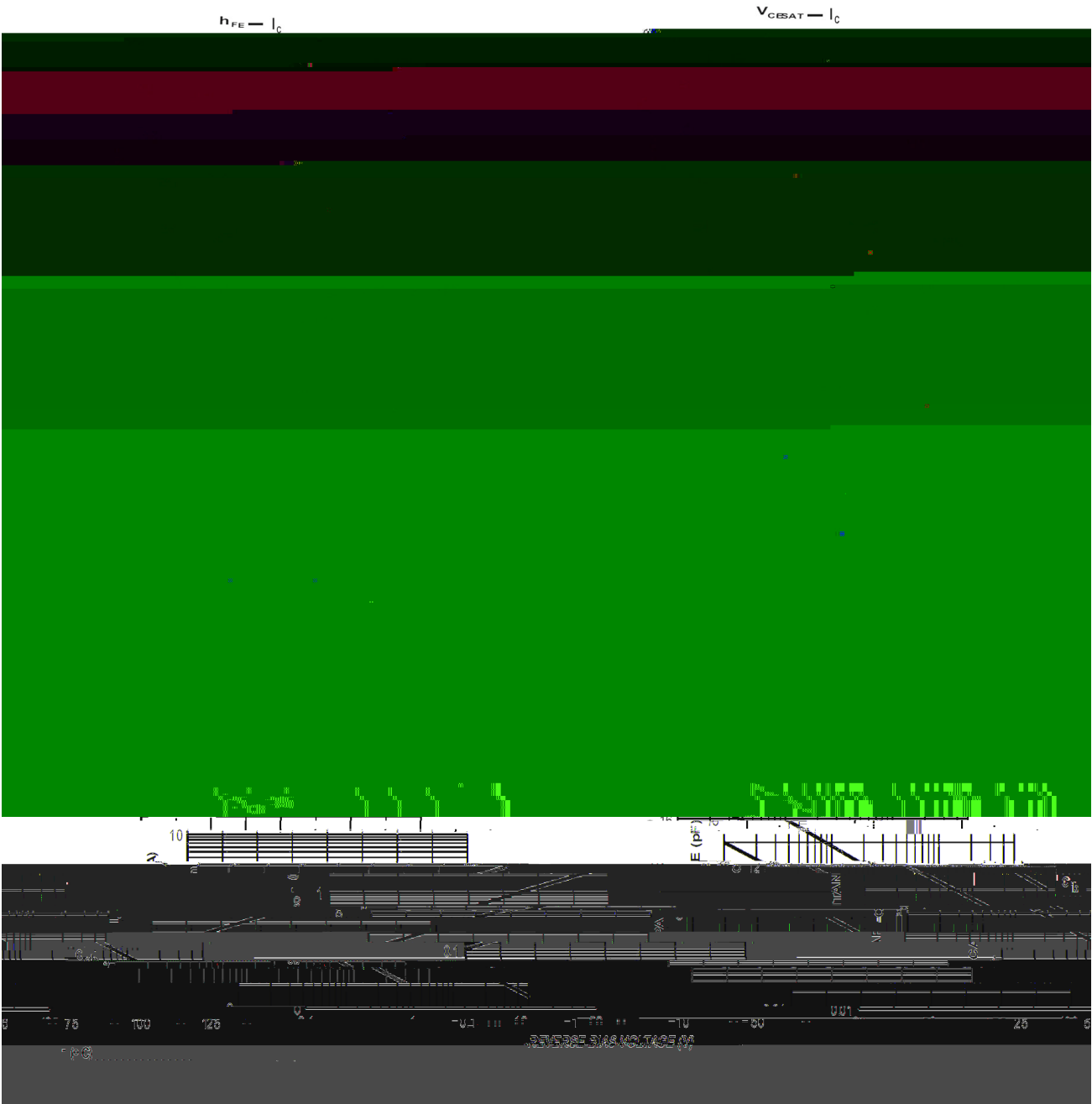
PIN 1 Base PIN 2 Emitter PIN 3 Collector

h _{FE} Range	100 300
Marking	Q2F

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-600	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

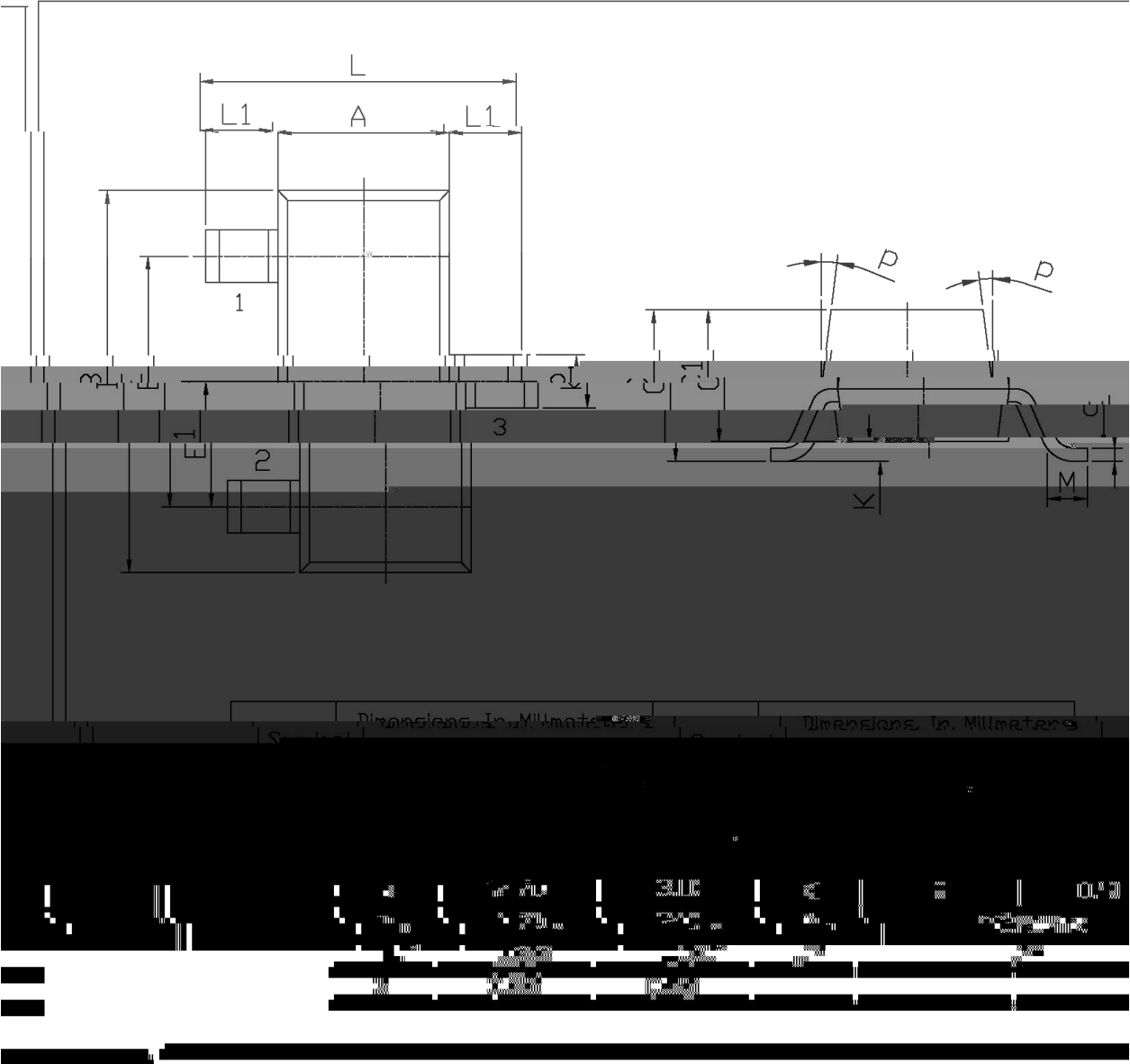
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\text{ A}$ $I_E = 0$	-60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10\text{ mA}$ $I_B = 0$	-60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\text{ A}$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -50\text{ V}$ $I_E = 0$			-0.01	A
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -10\text{ V}$ $I_C = -150\text{ mA}^*$	100		300	
	$h_{FE(2)}$	$V_{CE} = -10\text{ V}$ $I_C = -500\text{ mA}^*$	50			
	$h_{FE(3)}$	$V_{CE} = -10\text{ V}$ $I_C = -10\text{ mA}$	100			
	$h_{FE(4)}$	$V_{CE} = -10\text{ V}$ $I_C = -1.0\text{ mA}$	100			
	$h_{FE(5)}$	$V_{CE} = -10\text{ V}$ $I_C = -0.1\text{ mA}$	75		79D0	$T_c(8)$

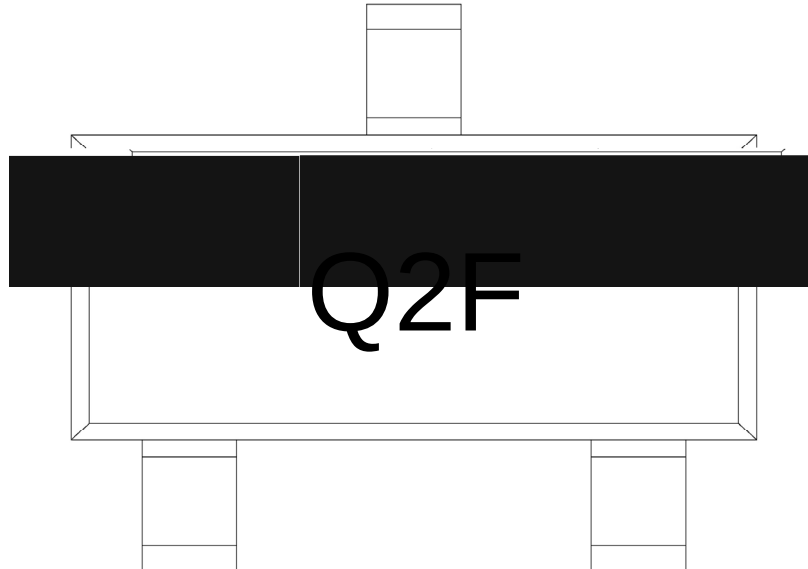
276.260



SUT-23

单位: mm





2F

Note:

Q: Automobile halogen-free product Code

2F Product Type Code

Whp shrdwxrh Prriioh irr IU Uhi0rw Vroghriq j+Pe-Frhh,

Note:

- 1

150 200

60 120sec;

1.Preheating:150~200 , Time:60~120sec.
- 2

255 5

5 0.5sec;

2.Peak Temp.:255 5 , Duration:5 0.5sec.
- 3

2 10

/sec.

3.Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL